

ABSTRACT OF THE DISCLOSURE

A light emitting device comprises a substrate, an epitaxial structure positioned on the substrate, an ohmic contact electrode positioned on the epitaxial structure and a current blocking structure positioned in the epitaxial structure. The epitaxial structure comprises a bottom cladding layer, an upper cladding layer, a light-emitting layer positioned between the bottom and the upper cladding layer, a window layer positioned on the upper cladding layer and a contact layer positioned on the window layer. The current blocking structure can extend from the bottom surface of the ohmic contact electrode to the light-emitting layer. According to the present invention, at least one ionic implanting process is performed to implant at least one proton beam into the epitaxial structure to form the current blocking structure.